

AMENDMENTSIn the Claims

This listing of claims will replace all prior versions, and listings, of claims in the application:

1. (Original) A mechanism for preventing ESD damage to a electronic device comprising at least one connection area having a plurality of pads (P_1 to P_n) arranged sequentially for mounting to an integrated circuit, and a plurality of fan-out signal lines (F_1 to F_n) extending from the pads (P_1 to P_n) respectively, the pads P_1 and P_n disposed on outermost sides of the connection area, the mechanism comprising:

a plurality of ESD protection device (ES_1 to ES_n) configured corresponding to the fan-out signal lines (F_1 to F_n);

wherein, equivalent impedances of the ESD protection devices ES_1 and ES_n are smaller than equivalent impedances of the other ESD protection devices ES_2 to ES_{n-1} .

2. (Original) The mechanism as claimed in claim 1, wherein each ESD protection device comprises at least one element having a MOS transistor circuit structure and equivalent channel widths of the ESD protection devices ES_1 and ES_n are longer than equivalent channel widths of the other ESD protection devices ES_2 to ES_{n-1} .

3. (Original) A mechanism for preventing ESD damage to a electronic device comprising at least one connection area having a plurality of pads (P_1 to P_n) arranged sequentially for mounting to an integrated circuit, and a plurality of fan-out signal lines (F_1 to F_n) extending

from the pads (P_1 to P_n) respectively, the pads P_1 and P_n disposed on outermost sides of the connection area, the mechanism comprising:

a plurality of ESD protection device (ES_1 to ES_n) configured corresponding to the fan-out signal lines (F_1 to F_n);

wherein, equivalent impedances of the ESD protection devices ES_1 to ES_j gradually increase and equivalent impedances of the ESD protection devices ES_{j+1} to ES_n gradually decrease, $1 < j < n$.

4. (Original) The mechanism as claimed in claim 3, wherein each ESD protection device comprises at least one element having a MOS transistor circuit structure, equivalent channel widths of the ESD protection devices ES_1 to ES_j gradually decrease, and equivalent channel widths of the ESD protection devices ES_{j+1} to ES_n gradually increase.

5. (Original) A mechanism for preventing ESD damage to a electronic device comprising at least one connection area having a plurality of pads (P_1 to P_n) arranged sequentially for mounting to an integrated circuit, and a plurality of fan-out signal lines (F_1 to F_n) extending from the pads (P_1 to P_n) respectively, the pads P_1 and P_n disposed on outermost sides of the connection area, the mechanism comprising:

a plurality of ESD protection device (ES_1 to ES_n) configured corresponding to the fan-out signal lines (F_1 to F_n);

wherein, an equivalent impedance of one ESD protection device ES_k is different from equivalent impedances of the other ESD protection devices, $1 \leq k \leq n$.

6. (Original) The mechanism as claimed in claim 5, wherein each ESD protection device comprises at least one element having a MOS transistor circuit structure and an equivalent channel width of the ESD protection device ES_k is different from equivalent channel widths of the other ESD protection devices.

7. (Original) A liquid crystal display panel, comprising:

a pixel array;

at least one connection area having a plurality of pads (P_1 to P_n) arranged sequentially for mounting to an integrated circuit, wherein the pads P_1 and P_n are disposed on outermost sides of the connection area;

a plurality of fan-out signal lines (F_1 to F_n) extending from the pads (P_1 to P_n) respectively; and

a plurality of ESD protection devices (ES_1 to ES_n) configured corresponding to the fan-out signal lines (F_1 to F_n);

wherein, equivalent impedances of the ESD protection devices ES_1 and ES_n are smaller than equivalent impedances of the other ESD protection devices ES_2 to ES_{n-1} .

8. (Original) The liquid crystal display panel as claimed in claim 7, wherein each ESD protection device comprises at least one element having a MOS transistor circuit structure and equivalent channel widths of the ESD protection devices ES_1 and ES_n are longer than equivalent channel widths of the other ESD protection devices ES_2 to ES_{n-1} .

9. (Original) The liquid crystal display panel as claimed in claim 8, wherein the equivalent channel widths of the ESD protection devices ES_1 to ES_j gradually decrease, and the equivalent channel widths of the ESD protection devices ES_{j+1} to ES_n gradually increase,
 $1 < j < n$.

10. (Original) A liquid crystal display panel, comprising:

a pixel array;

at least one connection area having a plurality of pads (P_1 to P_n) arranged sequentially for mounting to an integrated circuit, wherein the pads P_1 and P_n are disposed on outermost sides of the connection area;

a plurality of fan-out signal lines (F_1 to F_n) extending from the pads (P_1 to P_n) respectively; and

a plurality of ESD protection device (ES_1 to ES_n) configured corresponding to the fan-out signal lines (F_1 to F_n);

wherein, an equivalent impedance of one ESD protection device ES_k is different from equivalent impedances of the other ESD protection devices, $1 \leq k \leq n$.

11. (Original) The liquid crystal display panel as claimed in claim 10, wherein each ESD protection device comprises at least one element having a MOS transistor circuit structure and an equivalent channel width of the ESD protection device ES_k is different from equivalent channel widths of the other ESD protection devices.